

# Microwave dielectric properties of the spinel composition $Mg_{1+x}Ti_xAl_{2-2x}O_4$

A. BADEV<sup>a,b</sup>, I. ILIEV<sup>a</sup>, J.P. CAMBRONNE<sup>b</sup>, T. LEBEY<sup>b</sup>, A. BARNABE<sup>c</sup>, V. LEVCHEVA<sup>d</sup>

<sup>a</sup>Department of non-ferrous metals and semiconductors- UCTM, Sofia, Bulgaria

<sup>b</sup>Laboratory of Plasma and Conversion of Energy (LAPLACE), 31062 Toulouse cedex 9, France

<sup>c</sup>Centre for research in Materials and Engineering (CIRIMAT), 31062 Toulouse cedex 9, France

<sup>d</sup>Department of Radiophysics, Physical Faculty of Sofia University Sofia, Bulgaria

The objects of our research is magnesium aluminates (spinel), in which the electric charge of  $Al^{3+}$  cation is partially substituted with constitutive trivalent cation of  $Mg^{2+}$  and  $Ti^{4+}$  in the system with the following composition:  $Mg_{1+x}Ti_xAl_{2-2x}O_4$  with (x) varying from 0,1 to 0,6. X-ray diffraction data shows that within the above values of (x) the composition is a single phase spinel. The microwave basic parameters were measured as  $\epsilon_r$ ,  $\tan \delta$  and  $\tau_f$  respectively with the following values:  $\epsilon_r = 6-12$ ,  $\tan \delta = (1.5-3.5) \times 10^{-4}$  at 10 GHz and  $Q_f = 70\ 000 - 90\ 000$ , and  $\tau_f$  from -50 to -70 ppm/deg.

(Received August 7, 2007; accepted August 31, 2007)

**Keywords:** Substituted aluminates, Microwave properties, Structure

## 1. Introduction

It is known that for microwave dielectric materials with relatively high  $\epsilon_r$  in the range of 40, experimental difficulties exist at frequencies above 30 GHz, as the size of the resonator disks becomes very small, and therefore it is difficult to press and polish them. The size of the disks become acceptable when materials like spinels with  $\epsilon_r = 9-14$  are used. Monospinel of Zn and Mg have  $\epsilon_r = 8.5 - 8.7$ ,  $Q_f = 56000$  to  $69000$  at 12 GHz (respectively  $\tan \delta = 2 \times 10^{-4} - 1.7 \times 10^{-4}$ ). Unfortunately they have relatively high temperature coefficient of frequency  $\tau_f = -75$  to  $-79$  ppm/deg. Compensation of  $\tau_f$  could be achieved upon additives with opposite sign, like  $TiO_2$ . For example, systems like  $(1-x)MgAl_2O_4 \cdot xTiO_2$  or  $(1-x)ZnAl_2O_4 \cdot xTiO_2$  for  $x = 0.12$  to  $0.5$  have  $\epsilon_r = 9 - 14$  and  $\tau_f = -27$  to  $6.2$  ppm/deg [1- 5]. It is necessary to notice that these compositions are not electron equilibrated. Such materials have a sintering temperature of  $1400-1450$  °C, at which a spinel solid solution is formed and contains a cation ( $Ti^{4+}$ ) with different valence than  $Mg^{2+}$  and  $Al^{3+}$  that could cause oxygen defects, and it therefore worsens dielectric losses.

The object of the present work is the study of  $MgAl_2O_4$ , in which  $Al^{3+}$  cations are partially substituted with constitutive trivalent cation  $Mg^{2+}$  -  $Ti^{4+}$  for the composition  $Mg_{1+x}Ti_xAl_{2-2x}O_4$  to be electron balanced, which represents a scientific and practical interest. We suppose that this substitution will lead to an increase of  $\epsilon_r$  and a probable decrease of  $\tau_f$ , keeping dielectric losses at  $10^{-4}$  rate.

## 2. Experimental procedure

As starting materials, MgO Fluka,  $TiO_2$  Kronos,  $Al_2O_3$  Fluka and  $CaCO_3$  Fluka with purity 98-99 % were used.

The synthesis is made by the conventional mixed oxide route. The ball milling and homogenization are made in agate milling pots and balls in deionized water in planetary ball mill Retsch during one hour. The dried mixture is calcined at  $1100$ °C for three hours in corundum pots. After drying, 0.3 %  $B_2O_3$  is added to ease the sintering process, and thereafter a secondary milling is made. Press-powder is made from the dried mixture, using PVA (10% solution) as a binder agent. For the pressing process, we use a powder fraction of 0.25-0.5 mm grain size at a pressure of  $1.5$  t/cm<sup>2</sup>. The sintering is proceeded in super kantal furnace Linn, at different temperatures with isothermal maintaining during three hours. X-ray analysis is made from the powder material using  $CuK\alpha$  radiation in CIRIMAT-Toulouse.

The measurements of  $\epsilon_r$ ,  $\tan \delta$ , and  $\tau_f$  are made according Hakki and Koleman's method [6] modified by Courtney [7].

## 3. Results and discussions

### 3.1 X-Ray analysis

According to the ternary diagram of the  $MgO-Al_2O_3-TiO_2$  system at sintering temperatures between  $1400-1450$ °C, a solid solution which consists of  $MgAl_2O_4$  and  $TiMg_2O_4$  phases with a spinel structure is formed.

Fig. 1 presents the dependence between the lattice parameter calculated for different values of (x) by Végard law and the real measured one.

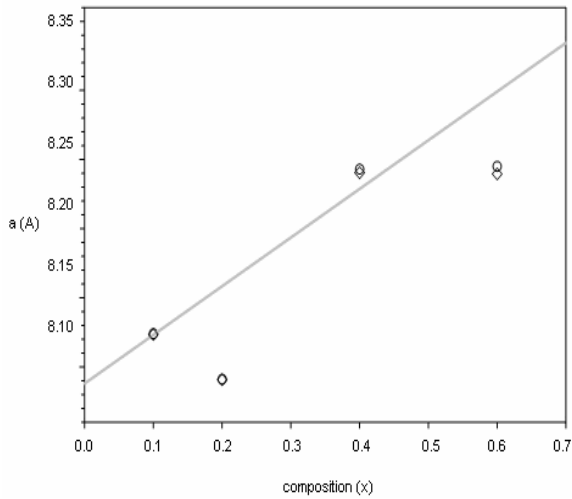


Fig. 1. Evolution of unit cell parameter as a function of the composition (x)

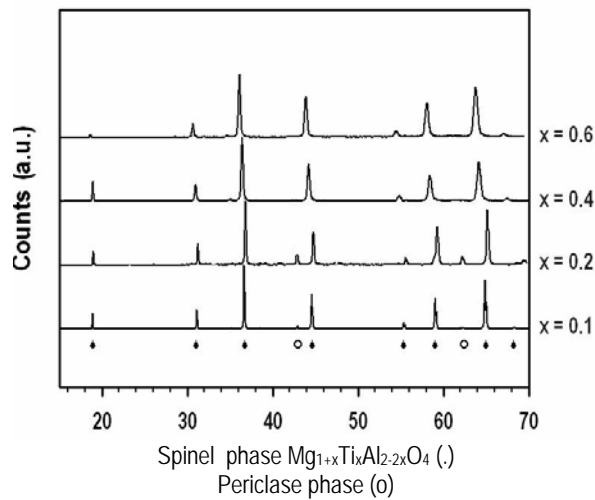


Fig. 2. XRD pattern of  $Mg_{1+x}Ti_xAl_{2-2x}O_4$  system sintered at  $1480^\circ C$ .

Fig.1 shows, that for all (x) values a spinel phase with lattice parameter varying from 8.1 to 8.25 is formed. Fig.2 confirms the appearance of the single phase spinel, as only for  $x=0.1$  a very small quantity of MgO did not react.

### 3.2 Microwave properties

On Fig. 3 is shown the relation between  $\epsilon_r$  and the composition (x) in the formula  $Mg_{1+x}Ti_xAl_{2-2x}O_4$ . The figure shows that  $\epsilon_r$  increases with (x) from 6 – 12, which is probably due to the increase of  $Ti^{4+}$  acting as a polarizing agent. Fig. 4 below shows that with increasing (x), dielectric losses move from  $1.5 \times 10^{-4}$  to  $3.5 \times 10^{-4}$

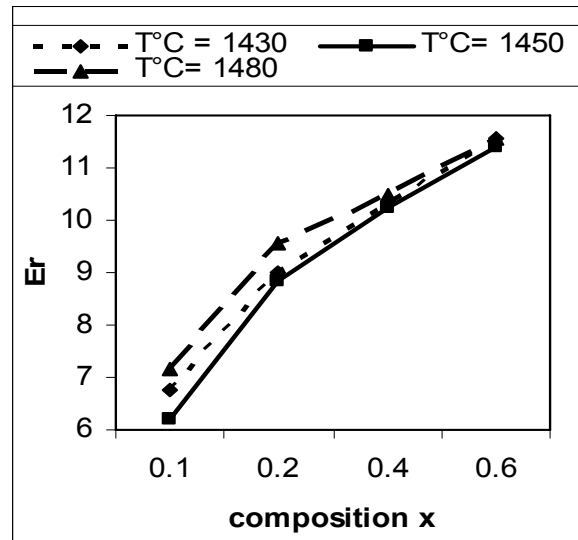


Fig. 3. Evolution of  $\epsilon_r$  with the composition (x).

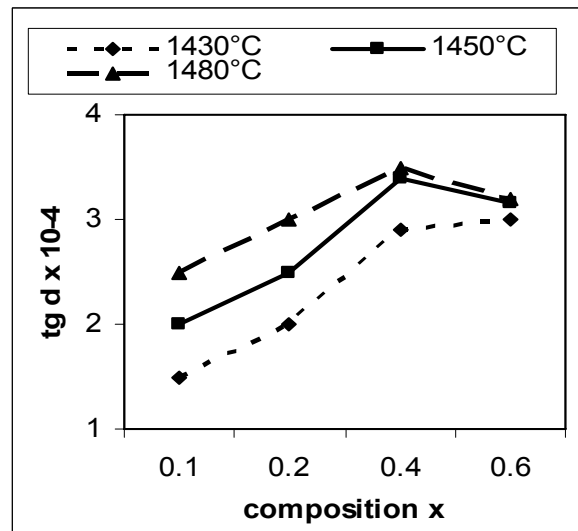


Fig. 4. Dielectric losses as a function of the composition (x).

Likely for all dielectric materials losses increase with  $\epsilon_r$  which is due to conductivity phenomenon and electron exchange between  $Ti^{4+}$  and  $Ti^{3+}$ . Therefore the quality factor which is related to dielectric losses, decreases with (x) content (from 90 000 to 33-40 000).

Fig 5. shows that the temperature coefficient of frequency  $\tau_f$  linearly decreases (from -70 to -50 ppm/deg) with composition (x).

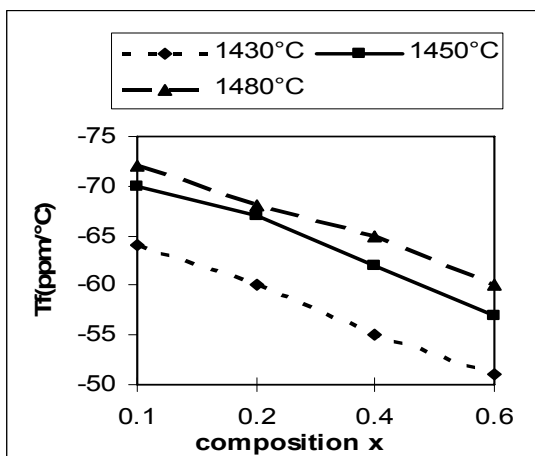


Fig. 5. Evolution of  $\tau_f$  with the composition ( $x$ )

This is due to a certain compensation of the temperature coefficient by the presence of  $Ti^{4+}$  cations. This compensation is lightly shown due to the presence of  $Mg^{2+}$  whose oxides have a  $\tau_f$  with an opposite sign than that of  $Ti^{4+}$  (respectively  $TiO_2$ ). The sintering temperature has a low impact on  $\epsilon_r$  but reflects on the losses and  $\tau_f$ . It is directly related to the microstructure (size of grains and porosity) and therefore affects losses  $\tan \delta$ . The optimal sintering temperature for our compositions appears to be 1430°C where losses and  $\tau_f$  are minimal.

#### 4. Conclusions

The following system  $Mg_{1+x}Ti_xAl_{2-2x}O_4$  (MTA) is studied, in which  $Al^{3+}$  cations are partially replaced with

constitutive trivalent cation  $Mg^{2+} - Ti^{4+}$  to preserve the stoichiometry and electronic balance between the positive and negative ions.

The synthesized obtained material is a single phase spinel.

The materials from the MTA system, especially those with  $x=0,1-0,2$  have very good microwave properties as  $\epsilon_r = 9-10$ ,  $\tan \delta = (1.5-3) \times 10^{-4}$  and  $Q_f = 70\,000 - 90\,000$  at 10 GHz, but unfortunately relatively high  $\tau_f = -50$  to  $-60$  ppm/deg within the same range as  $Al_2O_3$  and  $MgAl_2O_4$ . Therefore they are not suitable for microwave resonators, but they can be used as thin films for electronic circuits. One of our additional research showed that the MTA composition could be thermally compensated (50-60 ppm/°C) with substitutions of  $Ca^{2+}$ , which we will report in another paper.

#### References

- [1] K. P. Surendran, N. Santha, P. Mohanan and M.T. Sebastian, Eur. Phys. Journal **B.41**, 301-306 (2004).
- [2] M. T. Sebastian, A.T. Axelson, N. Alford, List of Microwave dielectric resonator materials, PEM-group, South Bank University, 25.11.2005.
- [3] M. N Alford, S. Penn, J. Appl. Phys. **80**, 5895 (1996).
- [4] J. Breeze, X. Aupi, N. Alford, Electronic letters **36**, 883 (2006).
- [5] Hakki, P. Coleman, IRE Trans. MTT **8**, 402 (1960).
- [6] W. Courtney, MTT **18**, 476 (1970).

\*Corresponding author: alex\_badev@yahoo.com